
HN62W448N Series

524288-word $\times$ 16-bit/1048576-word $\times$ 8-bit CMOS Mask
Programmable ROM

HITACHI

ADE-203-484A (Z)

Rev. 1.0

Jun. 6, 1997

Description

The Hitachi HN62W448N series is a 8-Mbit CMOS mask programmable ROM organized either as 524288-word $\times$ 16-bit or as 1048576-word $\times$ 8-bit. It has realized high speed normal access 120 ns and page mode access 50 ns on 3.3 V supply. It is the most suitable to the program and data memory for low voltage potable system. It has the package variations of standard 42-pin plastic DIP, standard 44-pin plastic SOP and standard 44-pin plastic TSOPII.

Features

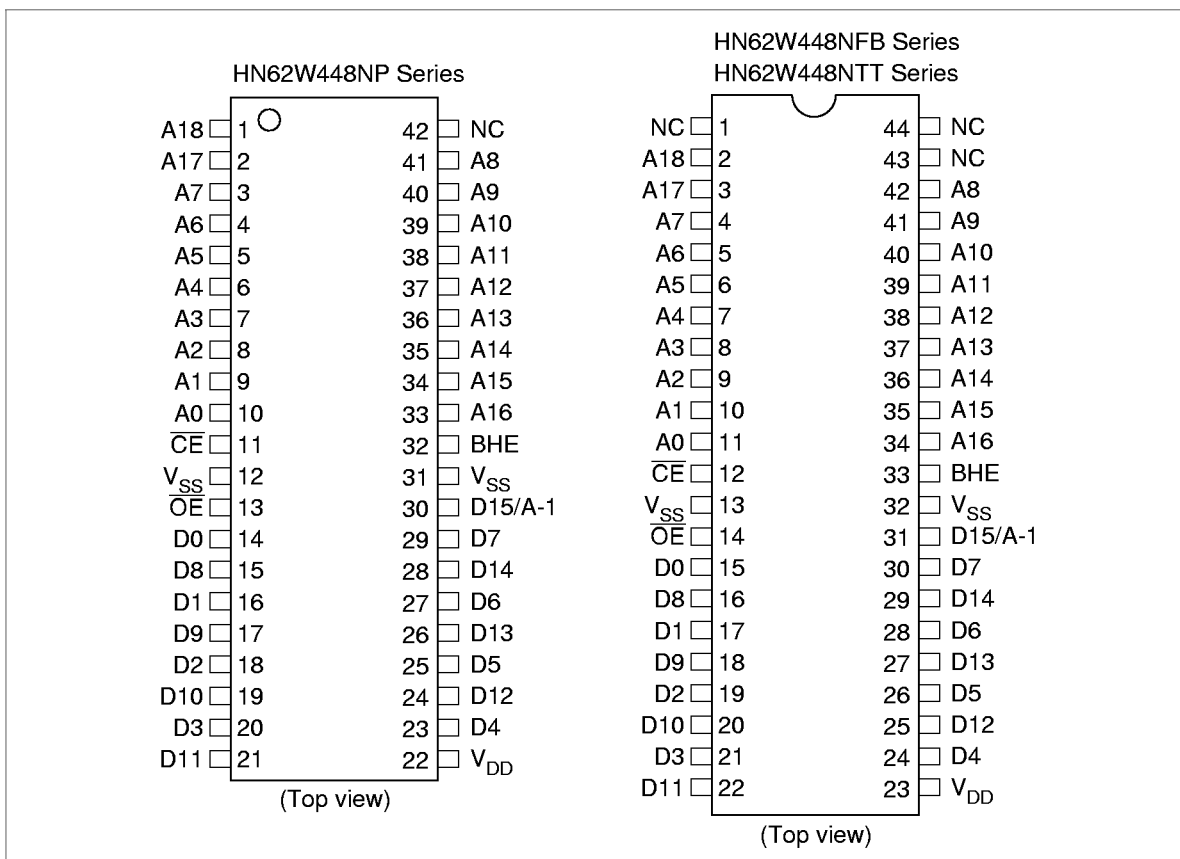
- Single 3.3 V supply : 3.3 V $\pm$ 0.3 V
- Access time:
 - Normal access time: 120 ns (max)
 - Page access time: 50 ns (max)
- Power dissipation
 - Active: 216 mW (max)
 - Standby: 108 μ W (max)
- Byte-wide or word-wide data organization with byte/word selection (BHE)
- 4-word page access on word-wide mode
- 8-byte page access on byte-wide mode
- Three-state data output for wired or-tying
- Directly LVTTL compatible all inputs and outputs

Ordering Information

Type No.	Access time	Package
HN62W448NP-12	120 ns	600-mil 42-pin plastic DIP (DP-42)
HN62W448NFB-12	120 ns	600-mil 44-pin plastic SOP (FP-44D)
HN62W448NTT-12	120 ns	400-mil 44-pin plastic TSOPII (TTP-44D)

HN62W448N Series

Pin Arrangement



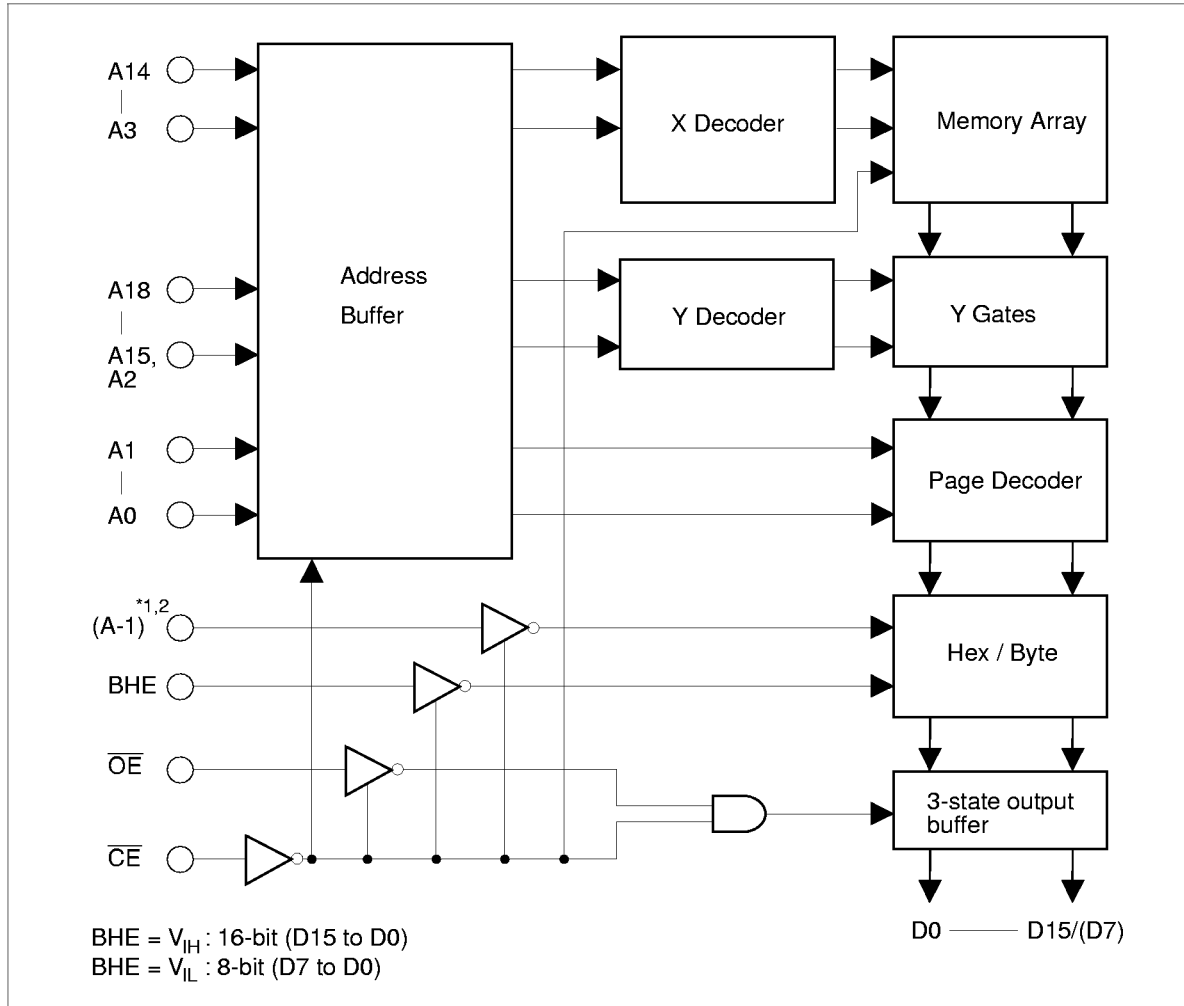
Pin Description

Pin name	Function
A2 to A18	Address input
A-1, A0, A1	Page address input
D0 to D15	Data output
$\overline{OE}$	Output enable
$\overline{CE}$	Chip enable
BHE	Byte/word selection
V_{DD}	Power supply
V_{SS}	Ground
NC	No connection

Block Diagram

Notes: 1. A-1 is least significant address.

2. When BHE is 'low', D14 to D8 goes the high impedance state, and D15 should be A-1.



Operation Table

Mode	$\overline{CE}$	$\overline{OE}$	BHE	D15/A-1	Data output		Address input	
					D0-D7	D8-D15	LSB	MSB
Standby	H	$\times^{*1}$	$\times$	$\times$	High-Z	High-Z	—	—
Output disable	L	H	$\times$	$\times$	High-Z	High-Z	—	—
Read (16-bit)	L	L	H	Dout	D0 to D7	D8 to D15	A0	A18
Read (8-bit)	L	L	L	L	D0 to D7	High-Z	A-1	A18
Read (8-bit)	L	L	L	H	D8 to D15	High-Z	A-1	A18

Note: 1. $\times$: Don't care.

HN62W448N Series

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Power supply voltage relative to V_{SS}	V_{DD}	-0.3 to +5.5	V
All input and output voltage relative to V_{SS}	V_{in} , V_{out}	-0.3 to $V_{DD} + 0.3$	V
Operating temperature range	T_{opr}	0 to +70	°C
Storage temperature range	T_{stg}	-55 to +125	°C
Temperature range under bias	T_{bias}	-20 to +85	°C

DC Operating Conditions ($T_a = 0$ to +70°C)

Parameter	Symbol	Min	Typ	Max	Unit
Supply voltage	V_{DD}	3.0	3.3	3.6	V
	V_{SS}	0	0	0	V
Input high voltage	V_{IH}	2.2	—	$V_{DD} + 0.3$	V
Input low voltage	V_{IL}	-0.3	—	0.8	V

DC Characteristics ($V_{DD} = 3.3 \text{ V} \pm 0.3 \text{ V}$, $V_{SS} = 0 \text{ V}$, $T_a = 0$ to +70°C)

Parameter	Symbol	Min	Max	Unit	Test conditions
Operating V_{DD} current	I_{DD}	—	60	mA	$V_{DD} = 3.6 \text{ V}$, $I_{DOUT} = 0 \text{ mA}$, $t_{RC} = 120 \text{ ns}$
Standby V_{DD} current	I_{SB1}	—	30	μA	$V_{DD} = 3.6 \text{ V}$, $\overline{CE} \geq V_{DD} - 0.2 \text{ V}$
	I_{SB2}	—	3	mA	$V_{DD} = 3.6 \text{ V}$, $\overline{CE} \geq 2.2 \text{ V}$
Input leakage current	$ I_{IL} $	—	10	μA	$V_{in} = 0$ to V_{DD}
Output leakage current	$ I_{OL} $	—	10	μA	$\overline{CE} = 2.2 \text{ V}$, $V_{OUT} = 0$ to V_{DD}
Output high voltage	V_{OH}	2.4	—	V	$I_{OH} = -2.0 \text{ mA}$
Output low voltage	V_{OL}	—	0.4	V	$I_{OL} = 2.0 \text{ mA}$

Capacitance ($V_{DD} = 3.3 \text{ V} \pm 0.3 \text{ V}$, $V_{SS} = 0 \text{ V}$, $T_a = 25^\circ\text{C}$, $V_{in} = 0 \text{ V}$, $f = 1 \text{ MHz}$)

Parameter	Symbol	Min	Max	Unit
Input capacitance	C_{in}	—	10	pF
Output capacitance	C_{out}	—	15	pF

AC Characteristics ($V_{DD} = 3.3 \text{ V} \pm 0.3 \text{ V}$, $V_{SS} = 0 \text{ V}$, $T_a = 0 \text{ to } +70^\circ\text{C}$)

Test Conditions

- Input pulse levels: 0.4 to 2.4 V
- Input rise and fall time: 5 ns
- Input and output timing reference levels: 1.4 V
- Output load: 1TTL + $C_L = 50 \text{ pF}$ (including jig)

Read Cycle

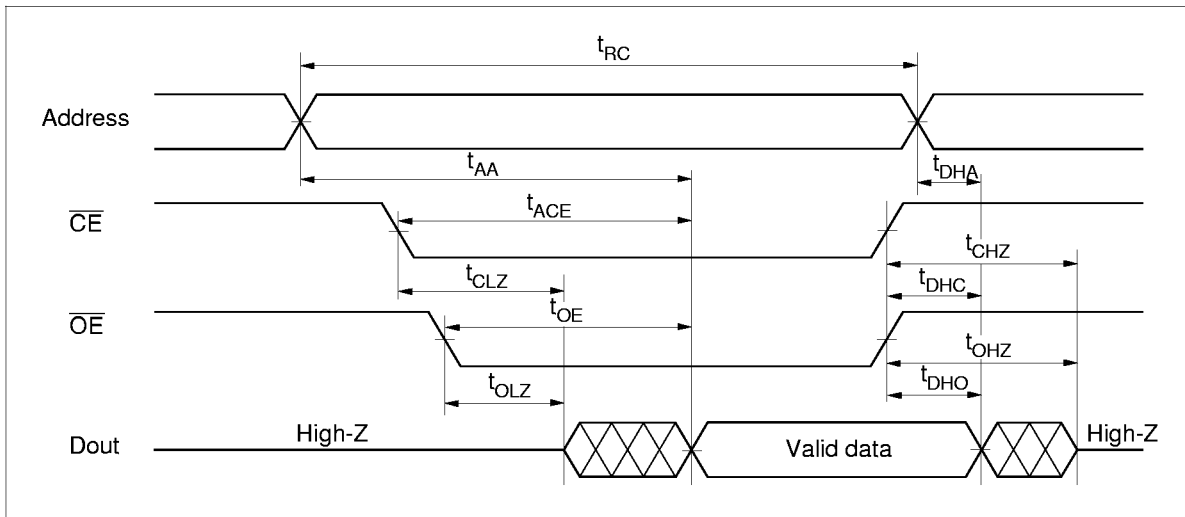
Parameter	Symbol	HN62W448N-12		Unit	Notes
		Min	Max		
Read cycle time	t_{RC}	120	—	ns	
Page read cycle time	t_{PC}	50	—	ns	
Address access time	t_{AA}	—	120	ns	3
Page address access time	t_{PA}	—	50	ns	
$\overline{CE}$ access time	t_{ACE}	—	120	ns	3
$\overline{OE}$ access time	t_{OE}	—	50	ns	3
BHE access time	t_{BHE}	—	120	ns	
Output hold time from address change	t_{DHA}	0	—	ns	2
Output hold time from $\overline{CE}$	t_{DHC}	0	—	ns	2
Output hold time from $\overline{OE}$	t_{DHO}	0	—	ns	2
Output hold time from BHE	t_{DHB}	0	—	ns	
$\overline{CE}$ to output in high-Z	t_{CHZ}	—	50	ns	1
$\overline{OE}$ to output in high-Z	t_{OHZ}	—	50	ns	1
BHE to output in high-Z	t_{BHZ}	—	50	ns	1
$\overline{CE}$ to output in low-Z	t_{CLZ}	5	—	ns	4
$\overline{OE}$ to output in low-Z	t_{OLZ}	5	—	ns	4
BHE to output in low-Z	t_{BLZ}	5	—	ns	

HN62W448N Series

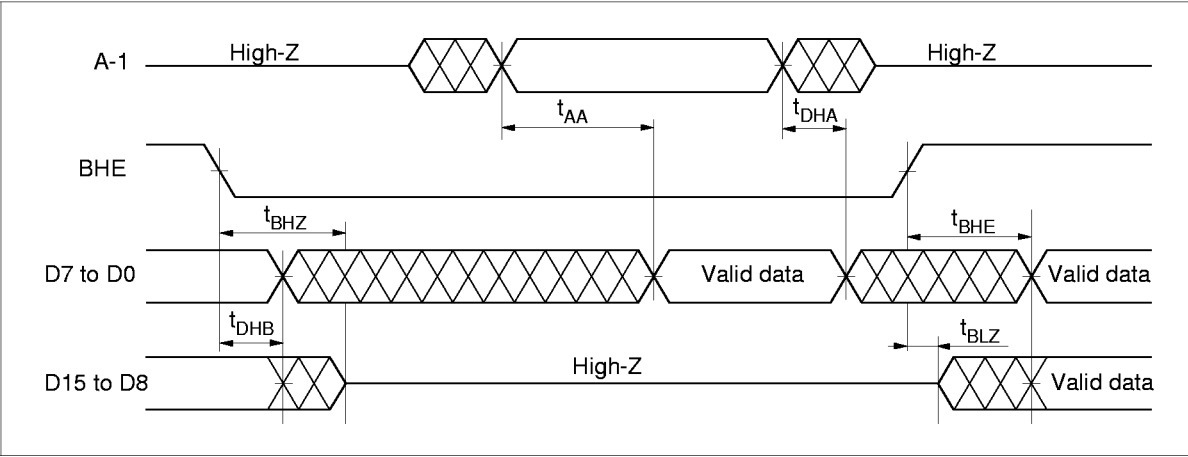
- Notes:
1. t_{CHZ} , t_{OHZ} and t_{BHZ} are defined as the time at which the output achieves the open circuit conditions and are not referred to output voltage levels.
 2. t_{DHA} , t_{DHC} , t_{DHO} : Determined by faster.
 3. t_{AA} , t_{ACE} , t_{OE} : Determined by slower.
 4. t_{CLZ} , t_{OLZ} : Determined by slower.
 5. $\overline{CE}$ and $\overline{OE}$ are enable A18 to A0 are valid.
 6. D15/A-1 pin is in the output state when BHE is high, $\overline{CE}$ and $\overline{OE}$ are enable. Therefore, the input signals of opposite phase to the output must be applied to them.
 7. Page address is determined as below.
Word mode (BHE = 'V_{IH}'): A0, A1
Byte mode (BHE = 'V_{IL}'): A-1, A0, A1
 8. $\overline{CE}$ and $\overline{OE}$ are enable.
 9. This device is used ATD (Address Transient Detector). Therefore, transfer either $\overline{CE}$ or address (A2 to A18) after power up to 3.0 V.

Timing Waveforms

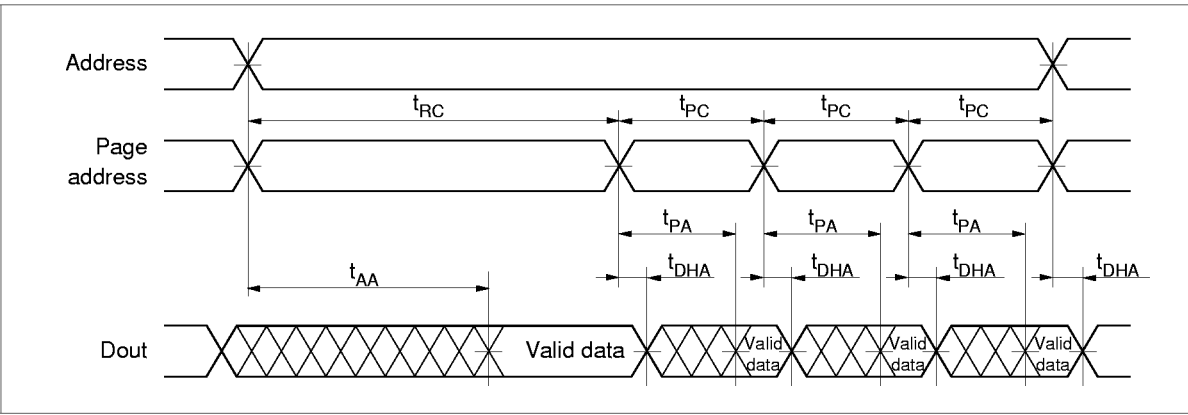
Word Mode (BHE = 'V_{IH}') or Byte Mode (BHE = 'V_{IL}')* 2, 3, 4



Word Mode, Byte Mode Switch*5, 6

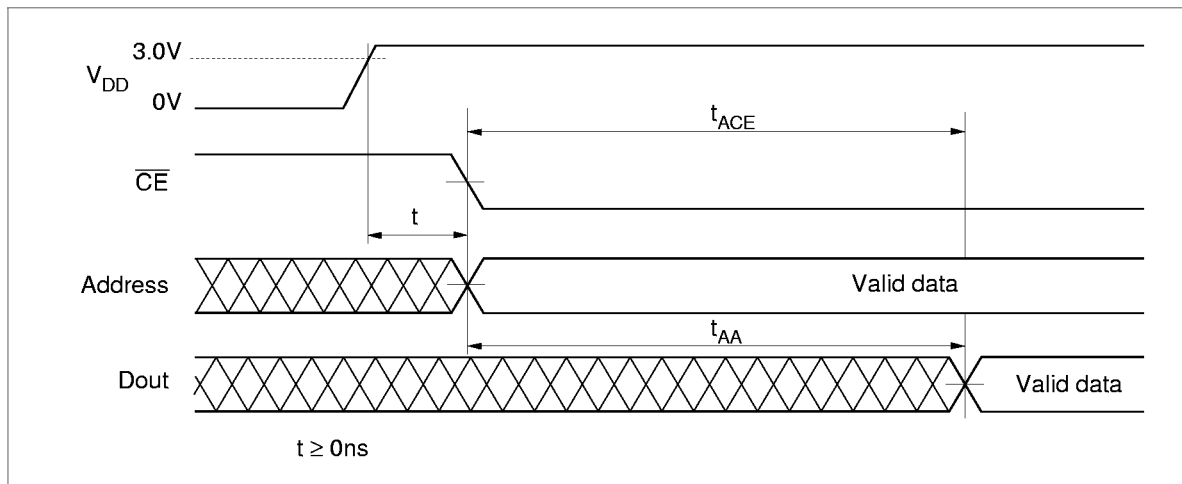


Page Mode*7, 8



HN62W448N Series

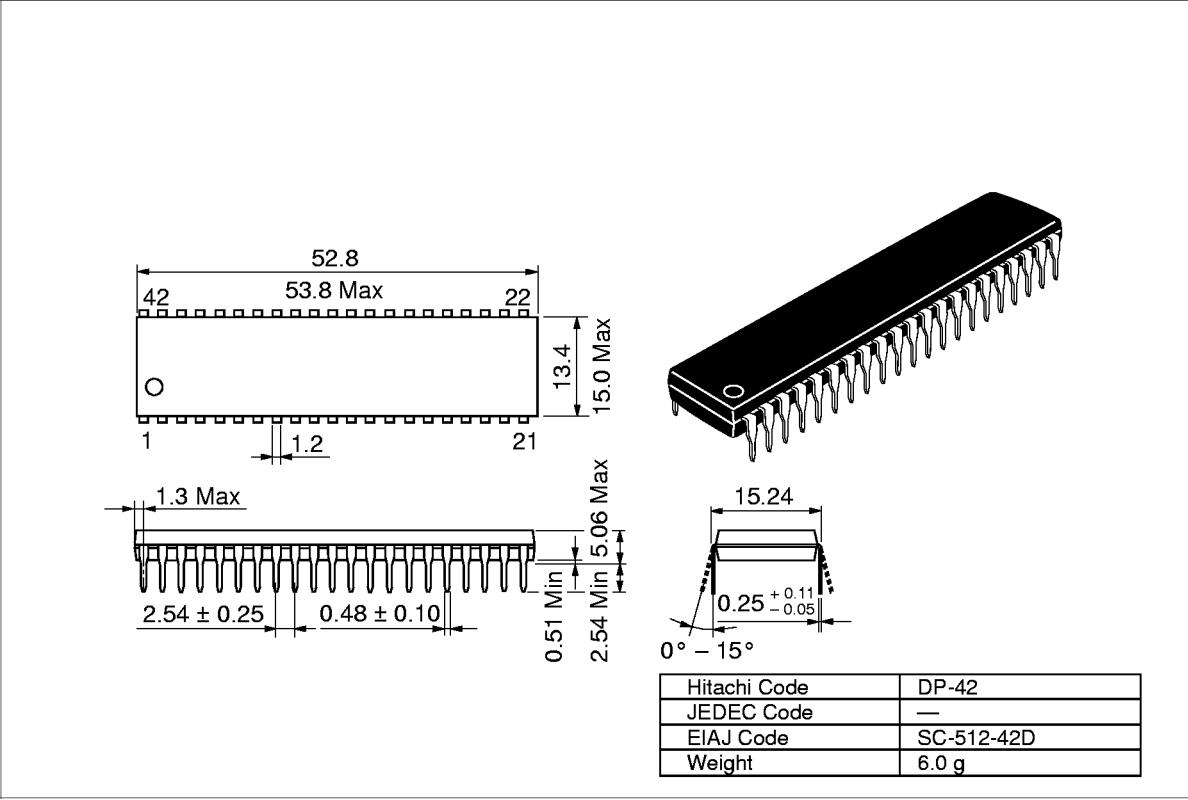
Power Up Sequence^{a*9}



Package Dimensions

HN62W448NP Series (DP-42)

Unit: mm

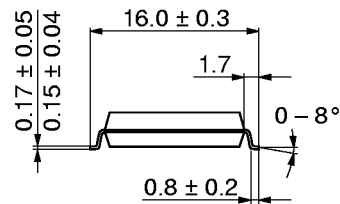
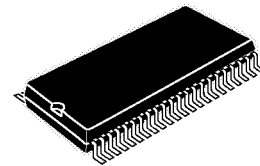
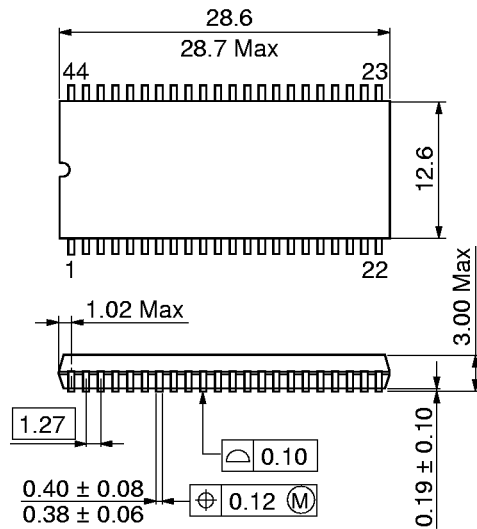


HN62W448N Series

Package Dimensions (cont.)

HN62W448NFB Series (FP-44D)

Unit: mm

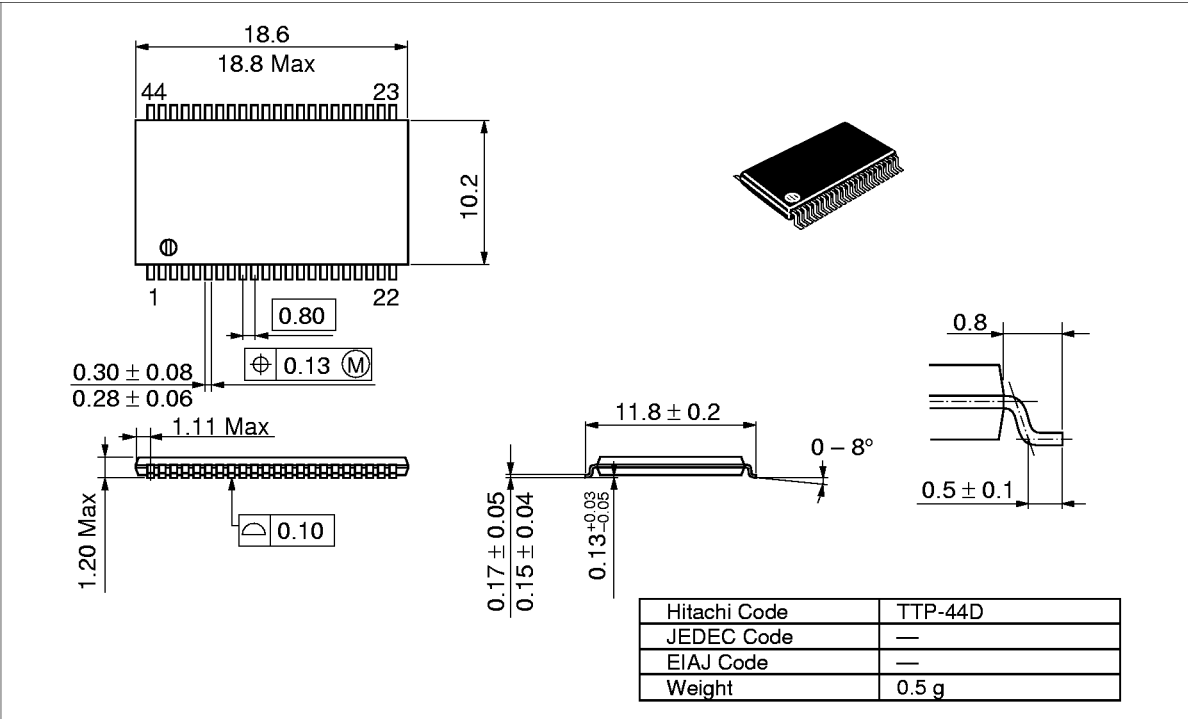


Hitachi Code	FP-44D
JEDEC Code	—
EIAJ Code	—
Weight	2.2 g

Package Dimensions (cont.)

HN62W448NTT Series (TTP-44D)

Unit: mm



HN62W448N Series

When using this document, keep the following in mind:

1. This document may, wholly or partially, be subject to change without notice.
2. All rights are reserved: No one is permitted to reproduce or duplicate, in any form, the whole or part of this document without Hitachi's permission.
3. Hitachi will not be held responsible for any damage to the user that may result from accidents or any other reasons during operation of the user's unit according to this document.
4. Circuitry and other examples described herein are meant merely to indicate the characteristics and performance of Hitachi's semiconductor products. Hitachi assumes no responsibility for any intellectual property claims or other problems that may result from applications based on the examples described herein.
5. No license is granted by implication or otherwise under any patents or other rights of any third party or Hitachi, Ltd.
6. **MEDICAL APPLICATIONS:** Hitachi's products are not authorized for use in MEDICAL APPLICATIONS without the written consent of the appropriate officer of Hitachi's sales company. Such use includes, but is not limited to, use in life support systems. Buyers of Hitachi's products are requested to notify the relevant Hitachi sales offices when planning to use the products in MEDICAL APPLICATIONS.

HITACHI

Hitachi, Ltd.

Semiconductor & IC Div.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100, Japan
Tel: Tokyo (03) 3270-2111
Fax: (03) 3270-5109

For further information write to:

Hitachi America, Ltd.
Semiconductor & IC Div.
2000 Sierra Point Parkway
Brisbane, CA. 94005-1835
U S A
Tel: 415-589-8300
Fax: 415-583-4207

Hitachi Europe GmbH
Electronic Components Group
Continental Europe
Dornacher Straße 3
D-85622 Feldkirchen
München
Tel: 089-9 91 80-0
Fax: 089-9 29 30 00

Hitachi Europe Ltd.
Electronic Components Div.
Northern Europe Headquarters
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA
United Kingdom
Tel: 0628-585000
Fax: 0628-778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 0104
Tel: 535-2100
Fax: 535-1533

Hitachi Asia (Hong Kong) Ltd.
Unit 706, North Tower,
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon
Hong Kong
Tel: 27359218
Fax: 27306071

Copyright © Hitachi, Ltd., 1997. All rights reserved. Printed in Japan.

Revision Record

Rev.	Date	Contents of Modification	Drawn by	Approved by
0.0	Nov. 22, 1995	Initial issue	Y. Yamada	T. Wada
0.1	Jun. 20, 1996	AC Characteristics Output load: 1TTL + C _L = 100 pF to 1TTL + C _L = 50 pF t _{PC} min: 60/70 ns to 50/70 ns t _{PA} , t _{OE} , t _{CHZ} , t _{OHZ} , t _{BHZ} max: 60/70 ns to 50/70 ns Deletion of timing Waveform for power up sequence	Y. Yamada	T. Wada
1.0	Jun. 6, 1997	Deletion of HN62W448N-15 Series AC Characteristics Addition of Note 8,9 Timing Waveform Addition of Power Up Sequence		